

Abstracts

High Efficiency Free Running Class F Oscillator

M. Prigent, M. Camiade, G. Pataut, D. Reffet, J.M. Nebus and J. Obregon. "High Efficiency Free Running Class F Oscillator." 1995 MTT-S International Microwave Symposium Digest 95.3 (1995 Vol. III [MWSYM]): 1317-1320.

A free running 1.6 GHz oscillator yielding 67 % power efficiency with 24 dBm output power is proposed. It is based on the use of a transistor working in the an high efficiency class F associated to an appropriate feedback network. The transistor is a 2 mm gate periphery, 0.7 μ m gate length MESFET and it is built by THOMSON foundry. The main impact of the characteristics of the constitutive components on the overall oscillator performance is also discussed.

[Return to main document.](#)